EGT3
ENGINEERING TRIPOS PART IIB

Friday, 29 ${ }^{\text {th }}$ April $2016 \quad$ 09:30-11:00

## Module 4B21

## ANALOGUE INTEGRATED CIRCUITS

Answer not more than three questions.

All questions carry the same number of marks.

The approximate percentage of marks allocated to each part of a question is indicated in the right margin.

Write your candidate number not your name on the cover sheet.

STATIONERY REQUIREMENTS
Single-sided script paper

SPECIAL REQUIREMENTS TO BE SUPPLIED FOR THIS EXAM<br>CUED approved calculator allowed<br>Attachment: 4B21 Analogue Integrated Circuits Data Sheet (2 pages).<br>Engineering Data Book

## 10 minutes reading time is allowed for this paper.

You may not start to read the questions printed on the subsequent pages of this question paper until instructed to do so.

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1 (a) With the aid of one or more circuit schematics, describe the operating principle of a current mirror and how one would scale the output current.
(b) The circuit shown in Fig. 1 is to be designed using a $0.18 \mu \mathrm{~m}$ CMOS process. The transistors have the following parameters: $\mu_{n} \cdot C_{o x}=387 \mu \mathrm{~A} \cdot \mathrm{~V}^{-2}, \mu_{p} \cdot C_{o x}=86 \mu \mathrm{~A} \cdot \mathrm{~V}^{-2}$, $V_{t n}=-V_{t p}=0.5 \mathrm{~V}, V_{D D}=1.8 \mathrm{~V}, V^{\prime}{ }_{A n}=5 \mathrm{~V} / \mu \mathrm{m}$, and $V^{\prime}{ }_{A p}=-6 \mathrm{~V} / \mu \mathrm{m}$. The output voltage is to swing between 0.2 V to 1.6 V and the voltage gain must be at least $10 \mathrm{~V} / \mathrm{V}$.
(i) Using the same channel length of transistors, design the circuit for a bias current of $50 \mu \mathrm{~A}$.
(ii) If the channel length is to be an integer multiple of $0.18 \mu \mathrm{~m}$, what is its value?
(iii) What is the new value of channel length if the gain is to be increased by a factor of 2 ?
(iv) What is the resulting increase in total gate area?
(c) State one application of the current mirror in a multi-stage amplifier.


Fig. 1

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2 (a) Explain what is meant by an ideal voltage source and an ideal current source.
(b) Shown in Fig. 2 are two common-base amplifiers, driven by an ideal voltage source Fig. 2 (a) and an ideal current source Fig. 2 (b), respectively.
(i) Assuming that each circuit has been properly biased, and that the biasing networks, which are not indicated in Fig. 2, do not affect the small-signal analysis, calculate the output resistance, $r_{\text {out }}$ for circuits (a) and (b), using the following data: $r_{\pi}=1 \mathrm{k} \Omega, r_{o}=100 \mathrm{k} \Omega$, and $\beta=100$.
(ii) Comment on the physical implications of the results for $r_{\text {out }}$ for each of the two configurations.


Fig. 2

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3 (a) With the aid of circuit block illustrations, define negative feedback, as applied to electronic circuits, describing its effect on circuit characteristics such as gain, linearity, input and output impedances, and bandwidth.
(b) What are the four negative feedback circuit topologies? State clearly whether the nature of the sampled and mixing signals is a voltage or current as applied to the different amplifier topologies.
(c) A feedback trans-resistance amplifier circuit is shown in Fig. 3. Assuming $R_{F} \gg$ $R_{C}$ and $r_{o} \gg R_{C}$ and that the feedback causes the signal voltage at the input node to be nearly zero:
(i) Derive expressions for $A \equiv V_{o} / I_{i}, \beta \equiv I_{f} / V_{o}$ and $A_{f} \equiv V_{o} / I_{s}$.
(ii) Find the value of $A_{f}$ for the case of $R_{C}=10 \mathrm{k} \Omega, R_{F}=100 \mathrm{k} \Omega$ and the transistor current gain $\beta=100$.


Fig. 3

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4 (a) Consider a MOSFET fabricated in $0.18 \mu \mathrm{~m}$ CMOS technology. With the aid of a device schematic, describe the main sources of capacitances (along with typical values) that influence high frequency circuit performance.
(b) With the aid of a simplified equivalent circuit, show that the MOSFET's unity gain frequency $\omega_{T}$ can be approximated as $\omega_{T}=g_{m} /\left(C_{g s}+C_{g d}\right)$, where $g_{m}$ is the transconductance, and $C_{g s}, C_{g d}$ the gate-source and gate-drain capacitances, respectively. [15\%]
(c) The components in the circuit shown in Fig. 4 have the following parameters: $\mu_{n} C_{o x}(W / L)=2 \mathrm{mAV}^{-2}, V_{t}=0.5 \mathrm{~V}, C_{g s}=C g d=10 \mathrm{fF}, R_{1}=100 \mathrm{k} \Omega, R_{G 1}=600 \mathrm{k} \Omega$, $R_{G 2}=1.4 \mathrm{M} \Omega, R_{D}=2 \mathrm{k} \Omega, R_{L}=10 \mathrm{k} \Omega, R_{S}=1 \mathrm{k} \Omega$ and $C_{C 1}=C_{C 2}=C_{S}=\infty$. The supply voltage $V_{D D}=1.8 \mathrm{~V}$ and Early voltage $\mathrm{V}_{\mathrm{A}}=-26 \mathrm{~V}$.
(i) Construct the small signal equivalent circuit.
(ii) Find the mid band voltage gain $v_{o} / v_{i}$
(iii) What is the approximate upper -3 dB frequency $f_{H}$ ?
(iv) Briefly comment, using intuitive-based reasoning, on the circuit's high frequency behaviour in relation to the common-source amplifier.


Fig. 4

5 (a) Give a short account of the applications in which integrated phase-lock loop architectures are commonly used.

In a frequency synthesiser design for a computer motherboard, a current-starved Voltage-Controlled Oscillator (VCO) comprising seven identical stages is to be designed, based on the circuit in Fig. 5. The figure shows a single stage of the circuit (comprising transistors $M 1, M 2, M 3$ and $M 4$ ), enclosed in dashed lines, and the current control circuit (M5 and M6).
(b) Complete the schematic circuit for the VCO, and explain its mode of operation, giving details of what determines the frequency of operation.
(c) The total capacitance being driven at the output node of each stage is 2 fF . Assume that the minimum value of the control voltage $V_{\text {invCo }}$ is equivalent to the threshold voltage for M5. The threshold voltage for all devices has magnitude 1 V . The supply voltage $V_{D D}$ is 5 V , and the maximum drain current in each stage is to be $100 \mu \mathrm{~A}$. Stating any other assumptions made,
(i) estimate the maximum frequency that can be generated.
(ii) develop an equation for the VCO gain, $K_{V}$, and estimate its value. Comment on the linearity that can be achieved.[20\%]
(d) With the help of a block diagram, explain how the VCO developed in parts (b) and (c) could be used in combination with other suitably chosen circuit elements to achieve a frequency synthesiser whose output frequency is to be exactly 4 times the frequency of a stable reference.


Fig. 5
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END OF PAPER

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## 4B21 ANALOGUE INTEGRATED CIRCUITS DATA SHEET

Bipolar Junction Transistors:
$i_{C}=\alpha i_{E} \quad i_{C}=\beta i_{B} \quad i_{B}=(1-\alpha) i_{E} \quad i_{E}=(\beta+1) i_{B}$
$\beta=\frac{\alpha}{1-\alpha} \quad \alpha=\frac{\beta}{\beta+1} \quad V_{T}=\frac{k T}{q}=25 m V$ at 300 K
$g_{m}=\frac{I_{C}}{V_{T}} \quad r_{\pi}=\frac{V_{T}}{I_{B}} \quad r_{e}=\frac{V_{T}}{I_{E}} \quad r_{o}=\frac{V_{A}}{I_{C}}$
MOSFETs:
$i_{D}=K\left[2\left(v_{G S}-V_{t}\right) v_{D S}-v_{D S}{ }^{2}\right] \quad K=\frac{1}{2} \mu C_{o x}\left(\frac{W}{L}\right)$
$i_{D}=K\left(v_{G S}-V_{t}\right)^{2}=\frac{k^{\prime}}{2}\left(\frac{W}{L}\right)\left(v_{G S}-V_{t}\right)^{2}$
$k^{\prime}=\mu C_{o x}$
$g_{m}=2 K\left(v_{G S}-V_{t}\right) \quad r_{o}=\frac{\left|V_{A}\right|}{I_{D}}$
Differential Amplifiers:
$v_{o}=A_{d} v_{d}+A_{c m} v_{c m}$
$C M R R=20 \log \left|A_{d} / A_{c m}\right|$
$A_{c m}=\frac{v_{o}}{v_{c m}}$
$A_{d}=\frac{v_{o}}{v_{d}}=g_{m} R_{D}$
OR
OR

$$
A_{c m}=\frac{\Delta R_{D}}{2 R} \quad A_{d}=\frac{\Sigma R_{C}}{\Sigma R_{E}}
$$

BJT small signal operation: $\quad i_{C 1} \approx \frac{\alpha I}{2}+\frac{\alpha I}{2 V_{T}} \frac{v_{d}}{2} \quad i_{C 2} \approx \frac{\alpha I}{2}-\frac{\alpha I}{2 V_{T}} \frac{v_{d}}{2}$

$$
R_{i d}=2(\beta+1)\left(r_{e}+R_{E}\right) \quad R_{E}=\text { emitter resistance }
$$

FET small signal operation: $\quad i_{D 1} \approx \frac{I}{2}+\left(\frac{I}{V_{G S}-V_{t}}\right) \frac{v_{i d}}{2} \quad i_{D 2} \approx \frac{I}{2}-\left(\frac{I}{V_{G S}-V_{t}}\right) \frac{v_{i d}}{2}$
Millers Theorem: $\quad C_{e q}=C_{\text {bridge }_{e}}(1-K) \quad K \equiv \frac{V_{2}}{V_{1}}$
Thermal Noise:

$$
\left\langle v_{n}^{2}\right\rangle=4 k T B R \quad k=1.38 \times 10^{-23} \mathrm{~J} / \mathrm{K}
$$

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Feedback Architectures and Properties:

|  | Series-Shunt | Series-Series | Shunt-Series | Shunt-Shunt |
| :---: | :---: | :---: | :---: | :---: |
| Feedback signal $\mathrm{Xf}_{\mathrm{f}}$ | Voltage | Voltage | Current | Current |
| Sampled signal $\mathrm{X}_{\text {o }}$ | Voltage | Current | Current | Voltage |
| To find input loop, set $^{1}$ | $\mathrm{V}_{\mathrm{o}}=0$ | $\mathrm{I}_{0}=0$ | $\mathrm{I}_{0}=0$ | $\mathrm{V}_{\mathrm{o}}=0$ |
| To find output loop, set $^{1}$ | $\mathrm{I}_{\mathrm{i}}=0$ | $\mathrm{I}_{\mathrm{i}}=0$ | $\mathrm{V}_{\mathrm{i}}=0$ | $\mathrm{V}_{\mathrm{i}}=0$ |
| Signal Source | Thevenin | Thevenin | Norton | Norton |
| $\beta=\mathrm{X}_{\mathrm{f}} / \mathrm{X}_{\mathrm{o}}$ | $\mathrm{V}_{\mathrm{f}} / \mathrm{V}_{\text {o }}$ | $\mathrm{V}_{\mathrm{f}} / \mathrm{I}_{\mathrm{o}}$ | $\mathrm{If}_{\mathrm{f}} / \mathrm{I}_{\text {o }}$ | $\mathrm{I}_{\mathrm{f}} / \mathrm{V}_{\text {o }}$ |
| $\mathrm{A}=\mathrm{X}_{0} / \mathrm{X}_{\mathrm{i}}$ | $\mathrm{A}_{\mathrm{v}}=\mathrm{V}_{0} / \mathrm{V}_{\mathrm{i}}$ | $\mathrm{G}_{\mathrm{M}}=\mathrm{I}_{0} / \mathrm{V}_{\mathrm{i}}$ | $\mathrm{A}_{\mathrm{I}}=\mathrm{I}_{0} / \mathrm{I}_{\mathrm{i}}$ | $\mathrm{R}_{\mathrm{M}}=\mathrm{V}_{\mathrm{o}} / \mathrm{I}_{\mathrm{i}}$ |
| $\mathrm{D}=1+\beta \mathrm{A}$ | $1+\beta \mathrm{A}_{\mathrm{v}}$ | $1+\beta \mathrm{G}_{\mathrm{M}}$ | $1+\beta \mathrm{A}_{\text {I }}$ | $1+\beta \mathrm{R}_{\mathrm{M}}$ |
| $\mathrm{A}_{\mathrm{f}}$ | $\mathrm{A}_{\mathrm{v}} / \mathrm{D}$ | $\mathrm{G}_{\mathrm{M}} / \mathrm{D}$ | $\mathrm{A}_{\mathrm{I}} / \mathrm{D}$ | $\mathrm{R}_{\mathrm{M}} / \mathrm{D}$ |
| $\mathrm{R}_{\text {if }}$ | $\mathrm{R}_{\mathrm{i}} \mathrm{D}$ | $\mathrm{R}_{\mathrm{i}} \mathrm{D}$ | $\mathrm{R}_{\mathrm{i}} / \mathrm{D}$ | $\mathrm{R}_{\mathrm{i}} / \mathrm{D}$ |
| $\mathrm{R}_{\mathrm{of}}$ | $\mathrm{R}_{0} /\left(1+\beta \mathrm{A}_{\mathrm{v}}\right)$ | $\mathrm{R}_{0}\left(1+\beta \mathrm{G}_{\mathrm{M}}\right)$ | $\mathrm{R}_{0}\left(1+\beta \mathrm{A}_{\mathrm{i}}\right)$ | $\mathrm{R}_{\mathrm{o}} /\left(1+\beta \mathrm{R}_{\mathrm{M}}\right)$ |
| $\mathrm{R}^{\prime}$ of $=\mathrm{R}_{\text {of }} \backslash \backslash \mathrm{R}_{\mathrm{L}}$ | R'o/D | $\mathrm{R}^{\prime}\left(1+\beta \mathrm{G}_{\mathrm{M}}\right) / \mathrm{D}$ | $\mathrm{R}^{\prime}\left(1+\beta \mathrm{A}_{\mathrm{i}}\right) / \mathrm{D}$ | R' ${ }_{\text {d }}$ D |

${ }^{1}$ This procedure gives the basic amplifier circuit without feedback but taking the loading of $\beta, \mathrm{R}_{\mathrm{L}}$, and $\mathrm{R}_{\mathrm{s}}$ into account.

